



ACE160P17A

P-Channel Enhancement Mode Field Effect Transistor

Description

The ACE160P17A uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or small power switching applications.

Features

- $V_{DS}=-60V$, $I_D=-17A$
- $R_{DS(ON)} \leq 125m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} \leq 160m\Omega @ V_{GS}=-4.5V$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit	
Drain-Source Voltage	V_{DSS}	-60	V	
Gate-Source Voltage	V_{GSS}	± 20	V	
Drain Current (Continuous)*AC	I_D	$T_A=25^\circ C$	-17	A
		$T_A=100^\circ C$	-10	
Drain Current (Pulsed)*B	I_{DM}	-30	A	
Power Dissipation	P_D	50	W	
Operating temperature / storage temperature	T_J/T_{STG}	-55~175	$^\circ C$	

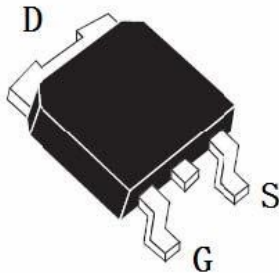
A: The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ C$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the $t \leq 10s$ junction to ambient thermal resistance rating.

Packaging Type

TO-252



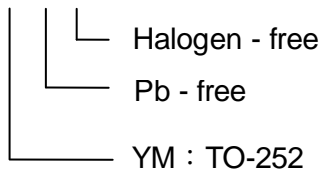


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Ordering information

ACE160P17A XX + H



Electrical Characteristics

$T_A=25^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Zero Gate Voltage Drain Current	I_{DSS1}	$V_{DS} = -48V, V_{GS} = 0V$			-1	μA
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_{DS} = -250\mu A$	-1.5		-3.5	V
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Drain-Source On-state Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -10A$		95	125	m Ω
		$V_{GS} = -4.5V, I_D = -5A$		123	160	
Forward Trans Conductance	g_{FS}	$V_{DS} = -5V, I_D = -10A$	8			S
Diode Forward Voltage	V_{SD}	$I_{SD} = -1A, V_{GS} = 0V$			-1.2	V
Maximum Body-Diode Continuous Current	I_S				-15	A
Switching						
Total Gate Charge	Q_g	$V_{DS} = -48V, I_D = -2A, V_{GS} = -10V$		15.8		nC
Gate-Source Charge	Q_{gs}			3		nC
Gate-Drain Charge	Q_{gd}			3.5		nC
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -10V, I_D = -1A, V_{GS} = -10V, R_G = 6\Omega$		9		ns
Turn-on Rise Time	t_r			10		ns
Turn-off Delay Time	$t_{d(off)}$			25		ns
Turn-off Fall Time	t_f			11		ns
Dynamic						
Input Capacitance	C_{iss}	$V_{DS} = -30V, V_{GS} = 0V, f = 1.0MHz$		987		pF
Output Capacitance	C_{oss}			114		pF
Reverse Transfer Capacitance	C_{rss}			46		pF



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Typical Performance Characteristics

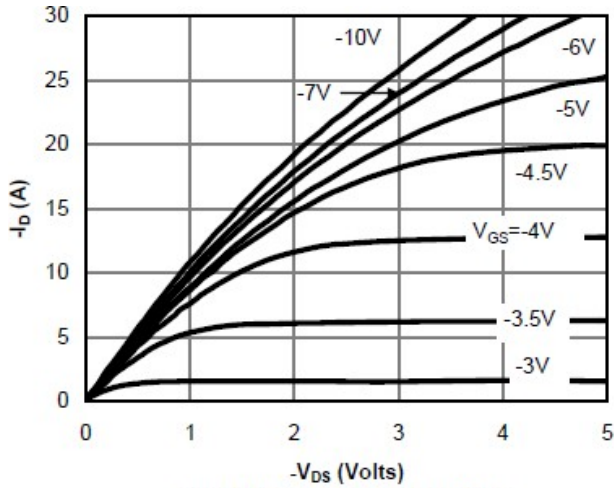


Fig 1: On-Region Characteristics

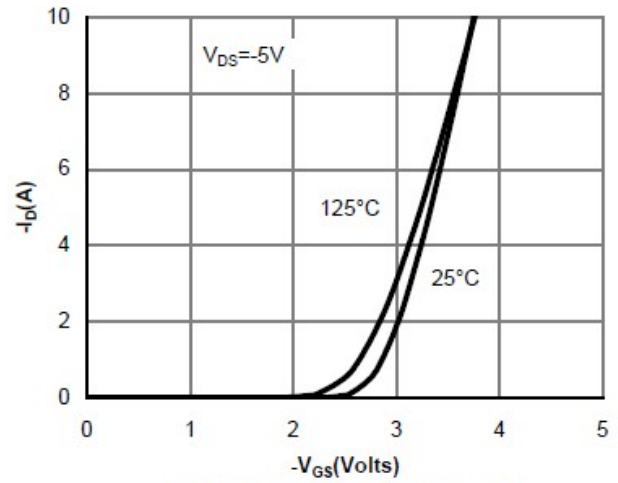


Figure 2: Transfer Characteristics

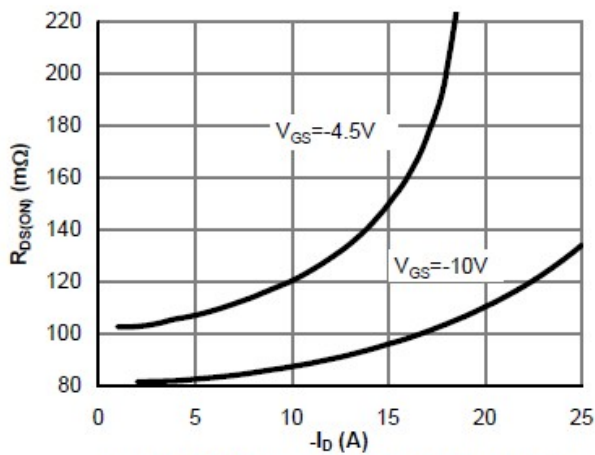


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

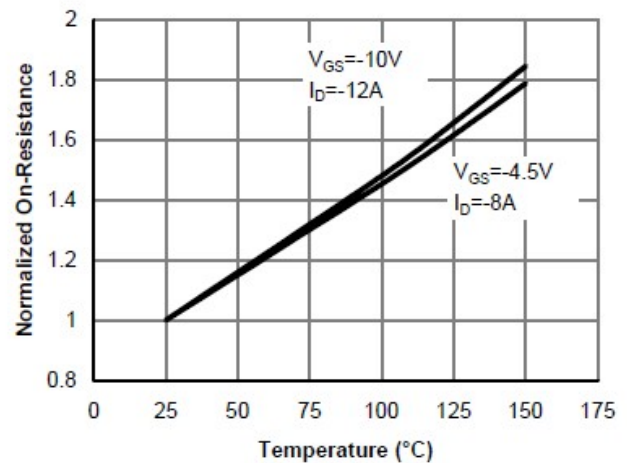


Figure 4: On-Resistance vs. Junction Temperature

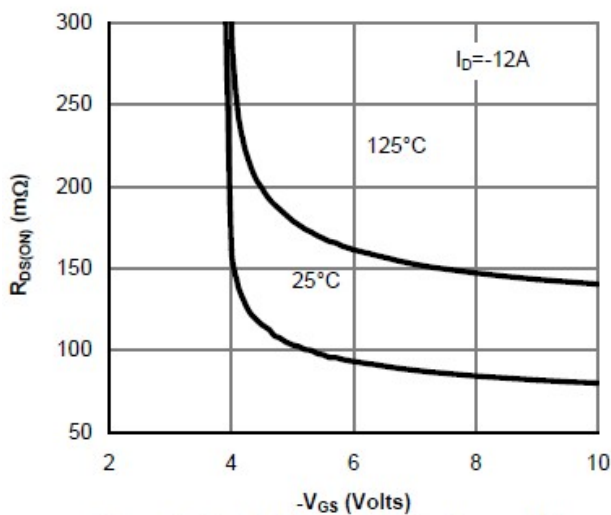


Figure 5: On-Resistance vs. Gate-Source Voltage

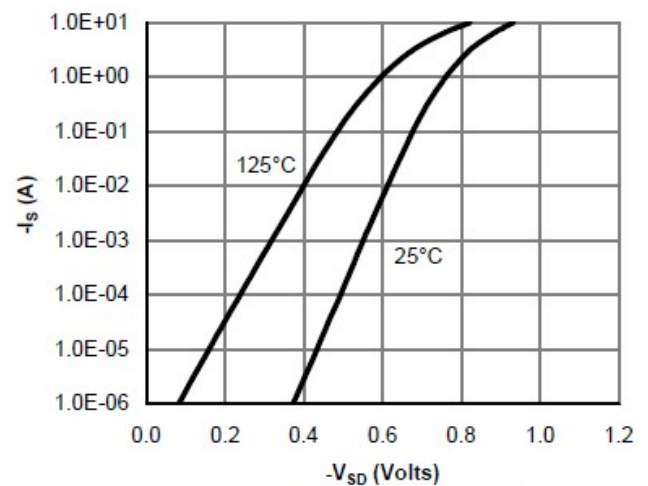


Figure 6: Body-Diode Characteristics



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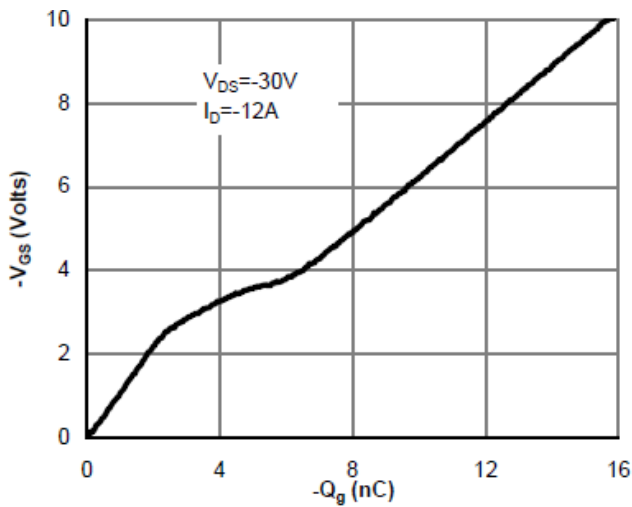


Figure 7: Gate-Charge Characteristics

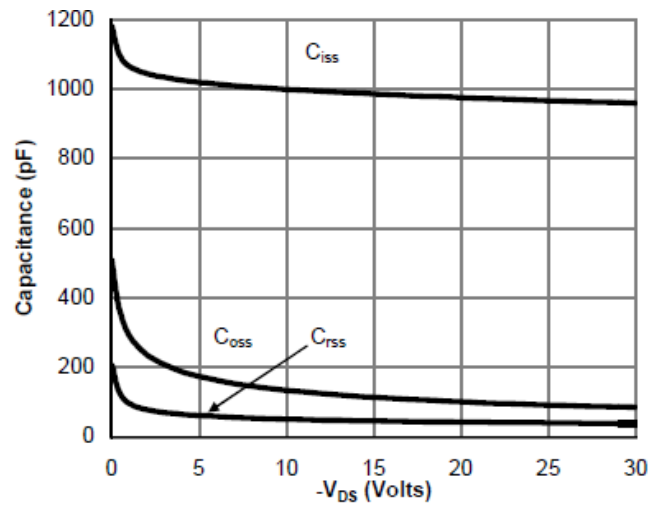


Figure 8: Capacitance Characteristics

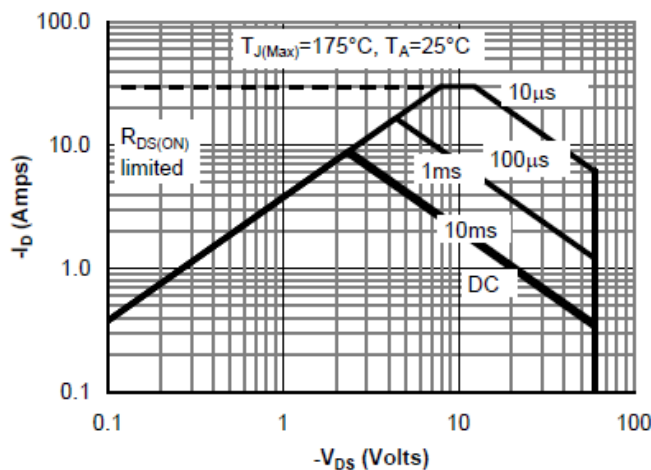


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

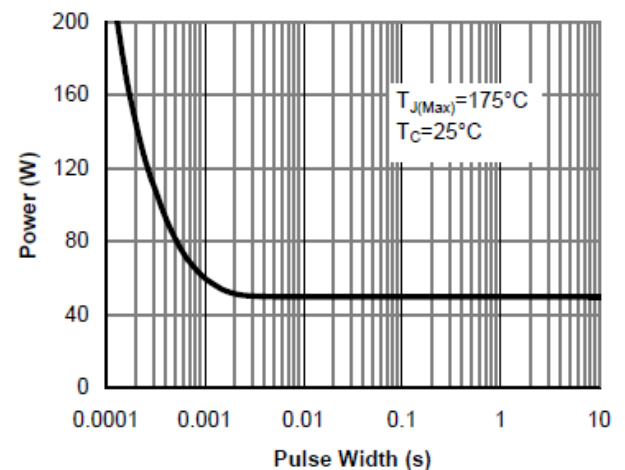


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

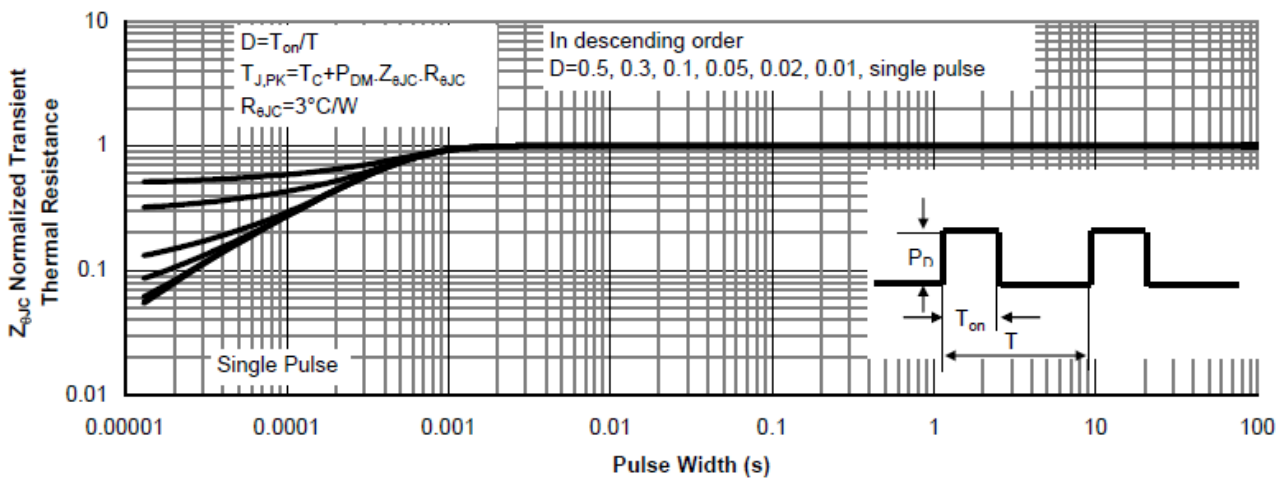


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

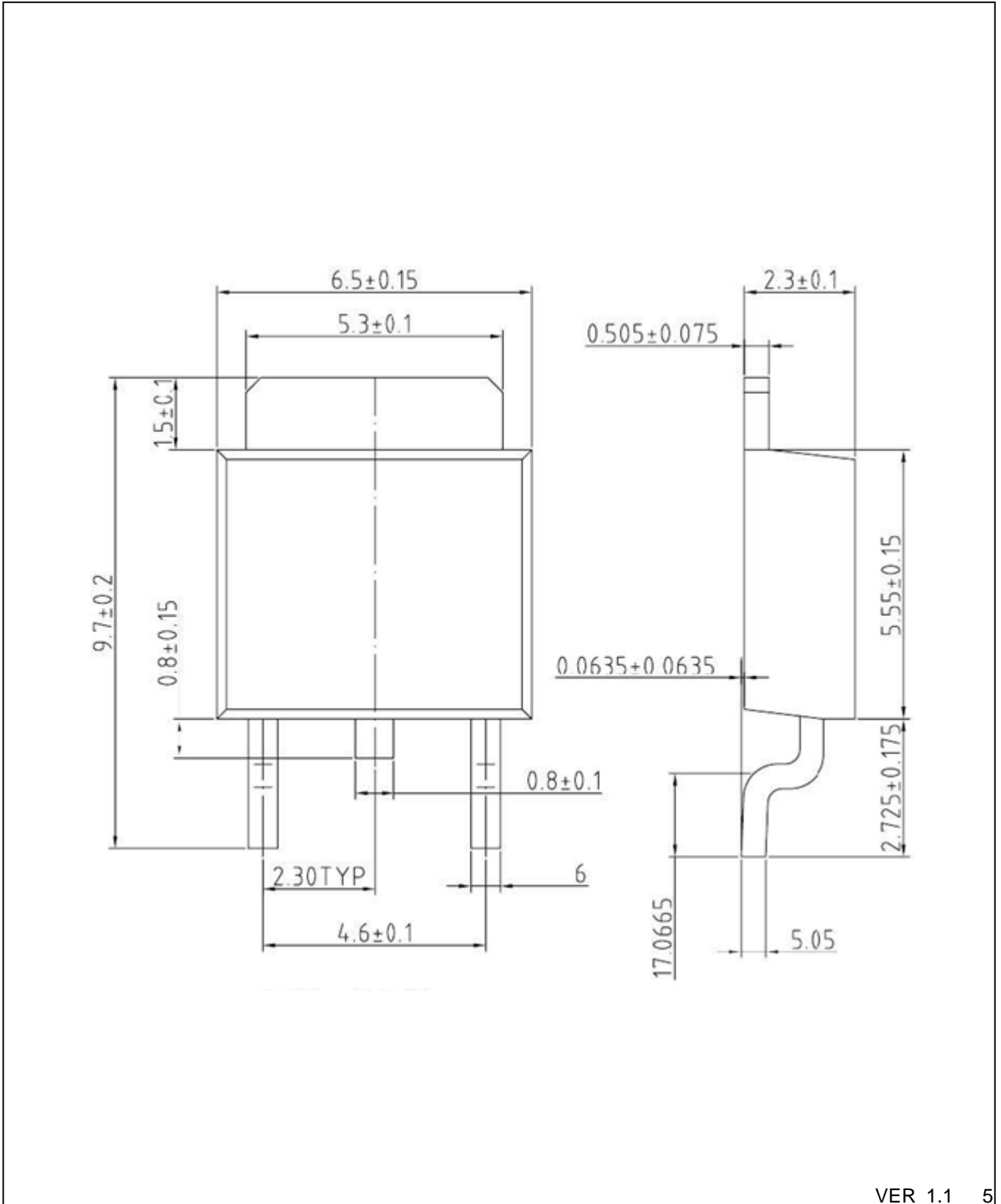


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Packing Information

TO-252





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Notes

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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